

Bibliography

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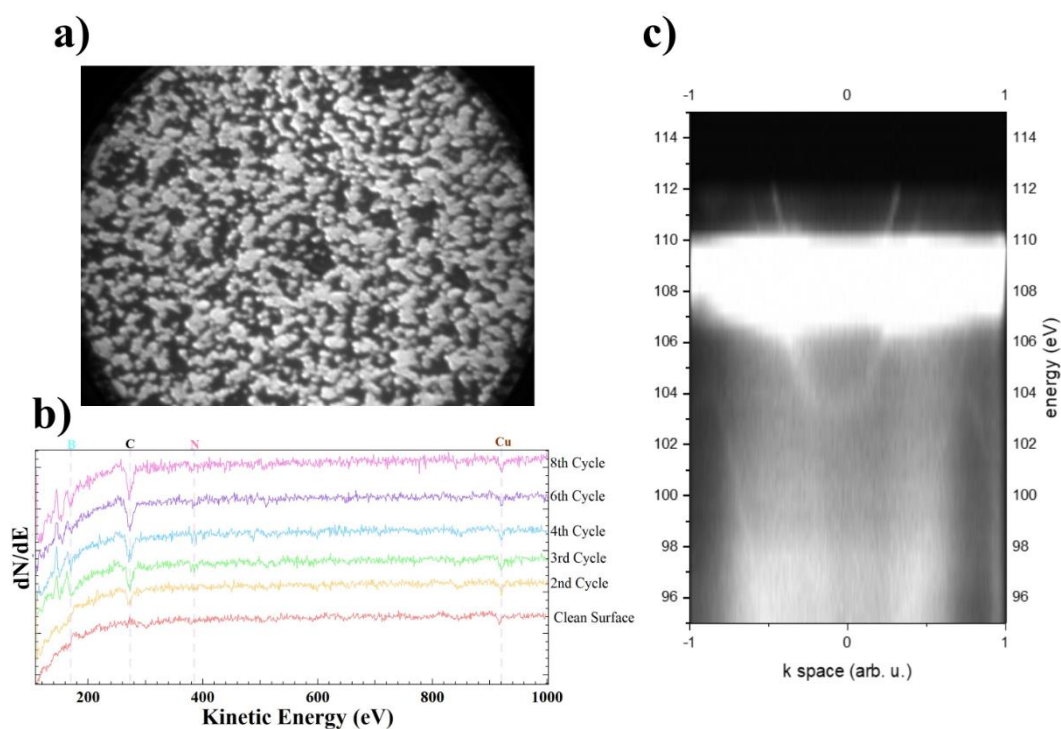


Figure 1: Boron nitride-doped graphene characterization. (a) Low Energy Electron Microscopy characterization after the 8th growth cycle. Energy: 5 eV, size: 4 μm . (b) Auger electron spectroscopy characterization performed after each of the growths cycles. HMB was introduced after the 3rd cycle. (c) Angle-Resolved Photoelectron Spectroscopy performed at a $h\nu = 115$ eV shows the band structure of boron nitride-doped graphene showing the lack of the Dirac cone, a clear indication of the presence of a bandgap.